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Supporting Information

Selectively Processible Instant Glue Passivation Layer for Indium–Gallium–Zinc Oxide Thin-Film Transistor Fabricating at Low Temperature

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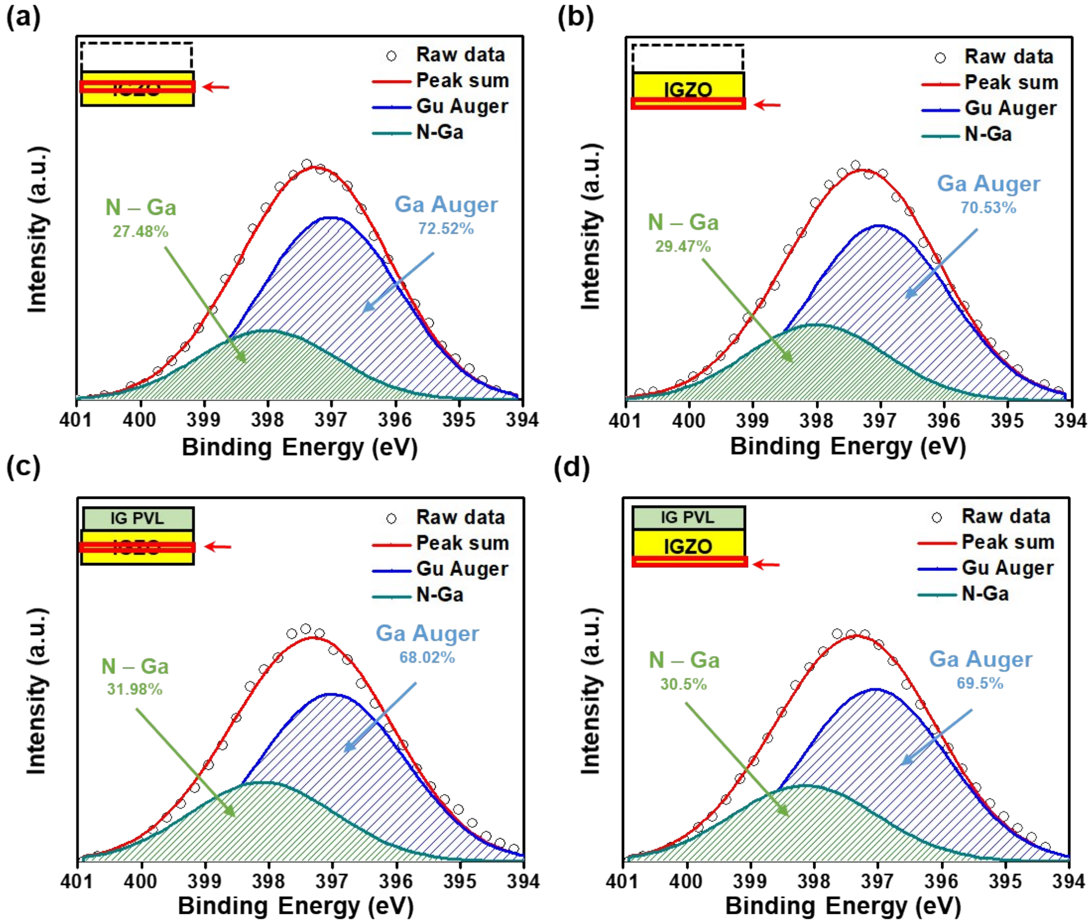

Figure S1. Deconvoluted XPS N1s spectra for (a) bulk channel and (b) front channel of IGZO films without PVL, and for (c) bulk channel and (d) front channel of IGZO films with IG PVL.

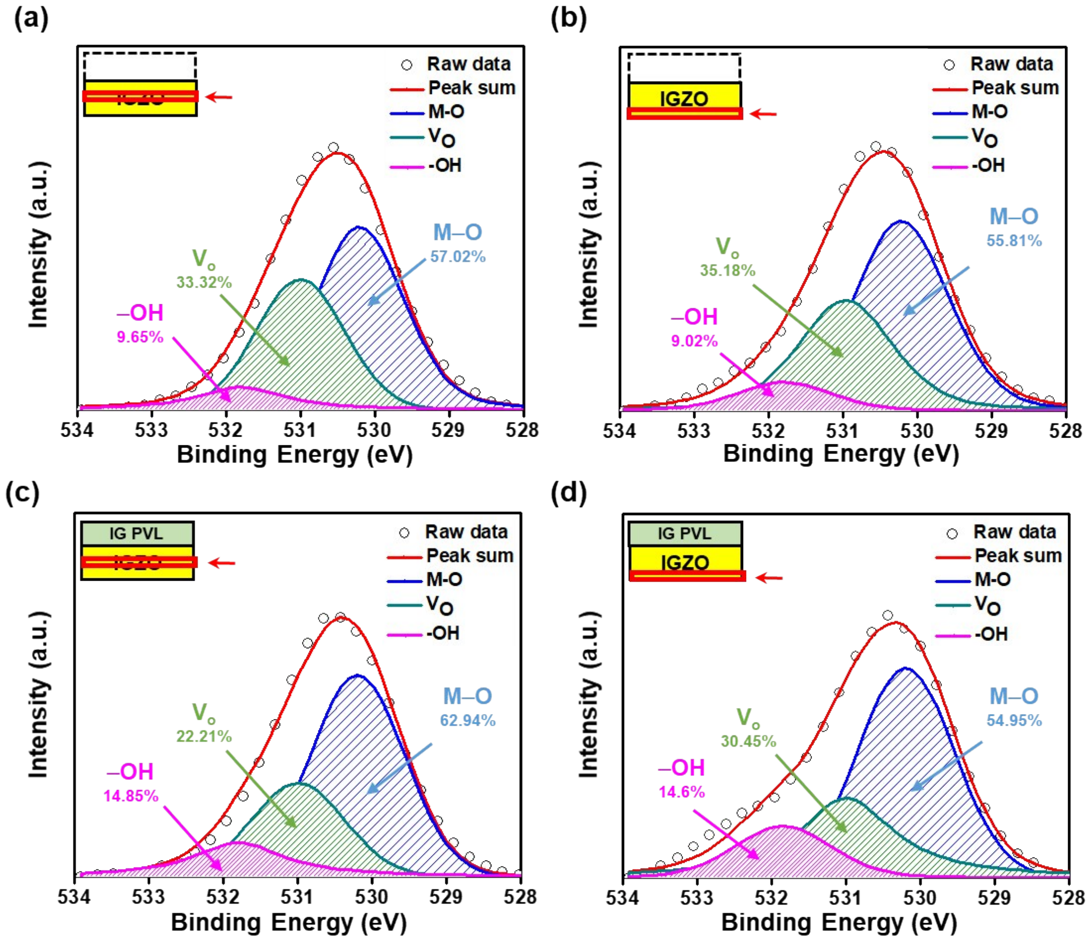

Figure S2. Deconvoluted XPS O1s spectra for (a) bulk channel and (b) front channel of IGZO films without PVL, and for (c) bulk channel and (d) front channel of IGZO films with IG PVL.